

FDH700

DISCRETE POWER AND SIGNAL TECHNOLOGIES

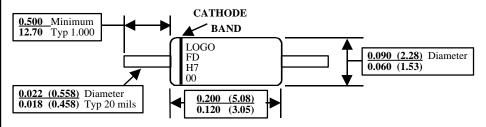
ULTRA FAST DIODE

Information Only Data Sheet FINAL REVERSE CURRENT & FORWARD VOLTAGE LIMITS MIGHT BE INCREASED SLIGHTLY

Absolute Maximum Ratings (note 1) TA = 25°C unless otherwise noted

Parameter	Value	Units
Storage Temperature	-65 to +200	°C
Maximum Junction Temperature	-65 to +175	οС
Total Power Dissipation at 25°C	250	mW
Derate above 25 ^o C	1.67	mW/ ^O C
Working Inverse Voltage	20	V
DC Forward Current	150	mA

Note 1: These ratings are limiting values above which the serviceability of any semiconductor device may be impaired



Electrical Characteristics

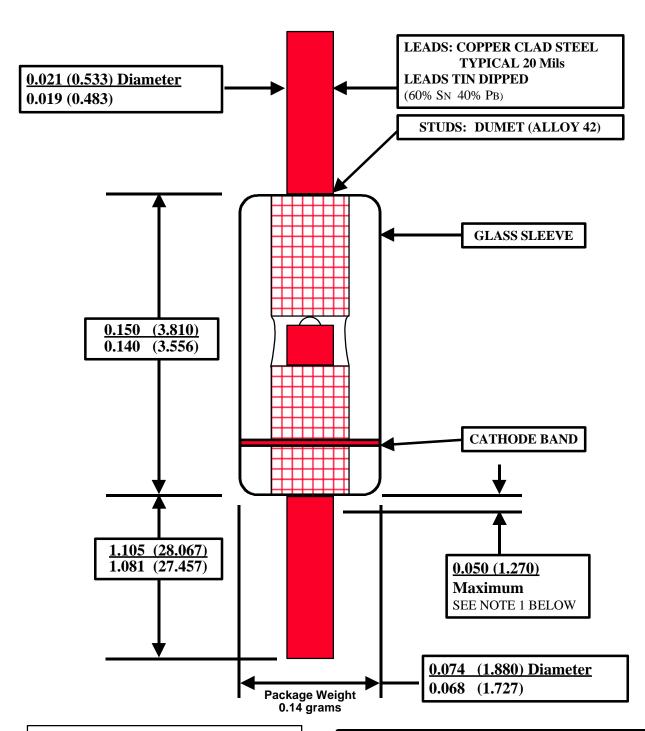
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SYM	CHARACTERISTICS	MIN	MAX	UNITS	TEST CONDITIONS
B_V	Breakdown Voltage	30		V	$I_R = 5.0 \text{ uA}$
I _R	Reverse Leakage		50 50	nA uA	$V_{R} = 20 \text{ V}$ $V_{R} = 20 \text{ V T}_{A} = 150^{\circ}\text{C}$
V _F	Forward Voltage	420 520 640 760 810 0.89	500 610 740 900 990 1.25	mV mV mV mV	$\begin{array}{lll} I_F & = & 10 \text{ uA} \\ I_F & = & 100 \text{ uA} \\ I_F & = & 1.0 \text{ mA} \\ I_F & = & 10 \text{ mA} \\ I_F & = & 20 \text{ mA} \\ I_F & = & 50 \text{ mA} \end{array}$
T _{RR}	Reverse Recovery Time		900	ps	$I_F = I_R = 10 \text{ mA } I_{RR} = 1.0 \text{ mA}$ $R_{Loop} = 100 \text{ Ohm}$
C _T	Diode Capacitance		1.5	pF	V _R = 0 V, f = 1.0 MHz



STANDARD DIGITAL MARKING CRITERIA

MAXIMUM CHARACTERS PER LINE: 3 MAXIMUM NUMBER OF LINES: 4 LOGO AND CHARACTERS M & W COUNT AS 2 CHARACTERS EACH



NOTE 1:

LEAD DIAMETER NOT CONTROLLED IN THIS ZONE TO ALLOW FOR FLASH, LEAD FINISH BUILD-UP, & MINOR IRREGULARITIES OTHER THAN SLUGS.

DO-35 PACKAGE

Fairchild Semiconductor's Criteria
11-MAR-97



FD700 Ultra Fast Diode Diode

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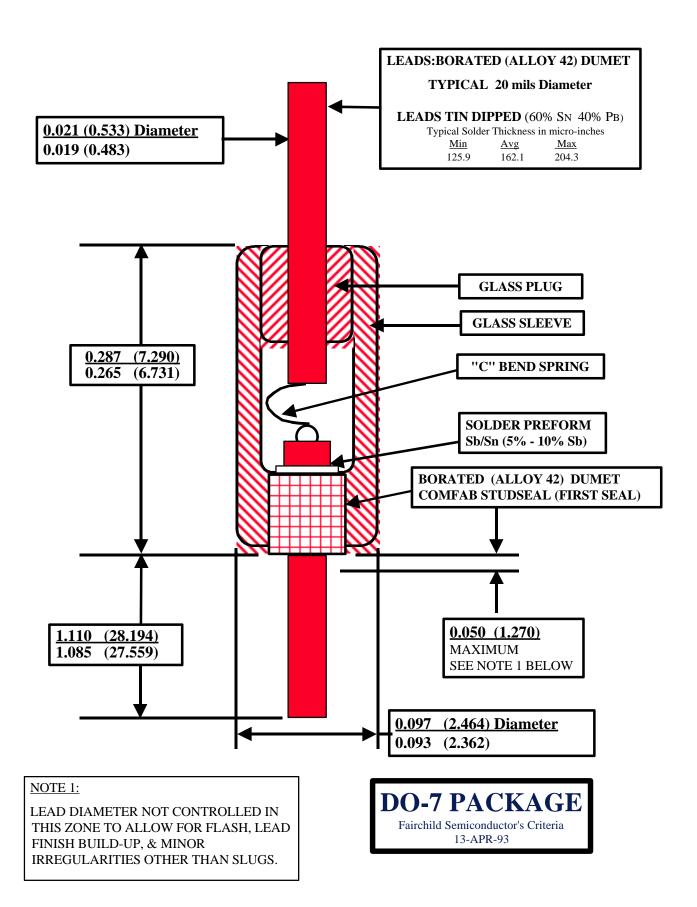


Electrical Characteristics

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SYM	CHARACTERISTICS	MIN	MAX	UNITS	TEST CONDITIONS
B_V	Breakdown Voltage	30		V	$I_R = 5.0 \text{ uA}$
I _R	Reverse Leakage		50 50	nA uA	$V_{R} = 20 \text{ V}$ $V_{R} = 20 \text{ V}$ $T_{A} = 150^{\circ}\text{C}$
V _F	Forward Voltage	420 520 640 760 810 0.89	500 610 740 880 950 1.10	mV mV mV mV V	$I_{F} = 10 \text{ uA}$ $I_{F} = 100 \text{ uA}$ $I_{F} = 1.0 \text{ mA}$ $I_{F} = 10 \text{ mA}$ $I_{F} = 20 \text{ mA}$ $I_{F} = 50 \text{ mA}$
T_RR	Reverse Recovery Time		700	ps	$I_F = I_R = 10 \text{ mA } I_{RR} = 1.0 \text{ mA}$ $R_{Loop} = 100 \text{ Ohm}$
C_T	Diode Capacitance		1.0	pF	V _R = 0 V, f = 1.0 MHz





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No Identification Needed	Full Production	This datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
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